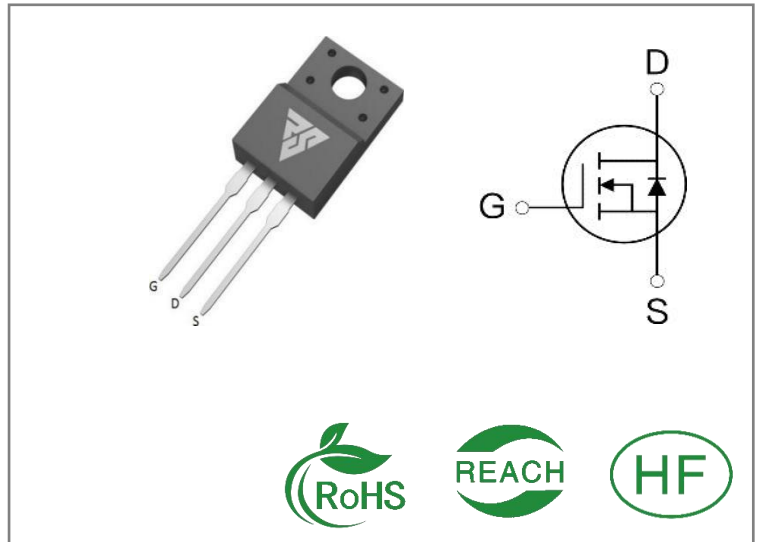


ID	R _{DS(ON)} (Typ)	V _{DSS}
11A	340mΩ	650V


Applications:

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- AC-DC Switching Power Supply

Features:

- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RS65R380F	T0-220F	RS65R380F	Tube	50 PCS

Absolute Maximum Ratings T_c = 25°C unless otherwise specified

Symbol	Parameter	RS65R380F	Units
V _{DSS}	Drain-to-Source Voltage	650	V
I _D	Continuous Drain Current TC=25°C	11	A
I _D	Continuous Drain Current TC=100°C	7	
I _{DM}	Pulsed Drain Current (Note*1)	33	
P _D	Power Dissipation	33	W
V _{GS}	Gate- to- Source Voltage	±30	V
EAS	Single Pulse Avalanche Energy L=10mH,V _{DS} = 50V, R _G = 25 Ω, TC=25°C	210	mJ
dv/dt	MOSFET dv/ dt ruggedness V _{DS} = 0...400V	50	V/ns
dv/dt	Reverse diode dv/dt V _{DS} = 0...400V, T _j = 25°C, I _{SD} ≤ I _D	15	V/ns
TL TPKG	Maximum Temperature for Soldering	300 260	°C
	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds		
T _J and T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	

* Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the“ Absolute Maximum Ratings” Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	RS65R380F	Units	Test Conditions
R θ JC	Junction-to-Case	3.6	°C / W	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 °C
R θ JA	Junction-to-Ambient	80		1 cubic foot chamber, free air.

OFF Characteristics T_J= 25°C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	650	--	--	V	VGS=0V, ID=250μA
IDSS	Drain- to- Source Leakage Current	--	--	1	μA	VDS=650V, VGS=0V
IGSS	Gate- to- Source Forward Leakage	--	--	100	nA	VGS=30V , VDS=0V
	Gate- to- Source Reverse Leakage	--	--	-100		VGS=-30V , VDS=0V

ON Characteristics T_J=25°C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On-Resistance(Note*2)	--	340	380	mΩ	VGS=10V, ID=5.5A
VGS(TH)	Gate Threshold Voltage	2	--	4	V	VGS=VDS, ID=250μA

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time	--	16.3	--	nS	VDS=400V ID=5.5A RG=25Ω
trise	Rise Time	--	35	--		
td(OFF)	Turn- OFF Delay Time	--	78	--		
tfall	Fall Time	--	39.5	--		

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Ciss	Input Capacitance	--	852	--	pF	VGS=0V VDS=100V f=1.0MHz
Coss	Output Capacitance	--	37	--		
Crss	Reverse Transfer Capacitance	--	2	--		
Qg	Total Gate Charge	--	19.2	--	nC	VDS=520V ID=5.5A VGS=10V
Qgs	Gate- to- Source Charge	--	3.1	--		
Qgd	Gate-to-Drain(" Miller") Charge	--	8.2	--		

Source- Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
IS	Continuous Source Current	--	--	11	A	Integral pn- diode in MOSFET
ISM	Maximum Pulsed Current	--	--	33	A	
VSD	Diode Forward Voltage	--	0.85	--	V	IS=5.5A,VGS=0V
trr	Reverse Recovery Time	--	310	--	nS	VR=100V IS=5.5A,di/dt=10 0A/μs
Qrr	Reverse Recovery Charge	--	2.8	--	μC	

Notes:

- * 1. Repetitive rating, pulse width limited by maximum junction temperature.
- * 2. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Feature Curve

Figure 1. Output Characteristics

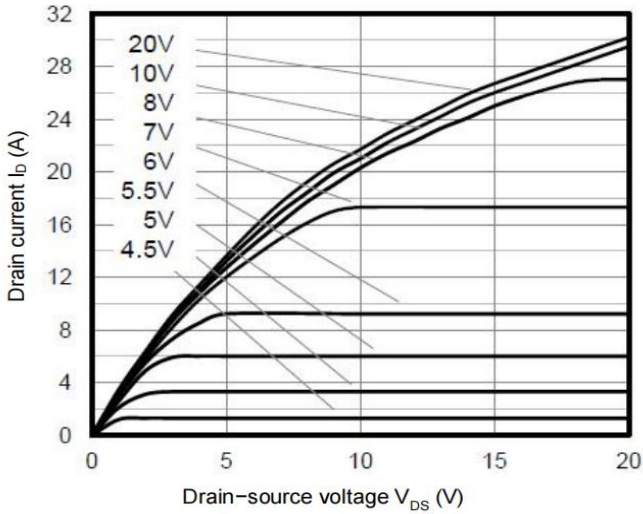


Figure 2. Transfer Characteristics

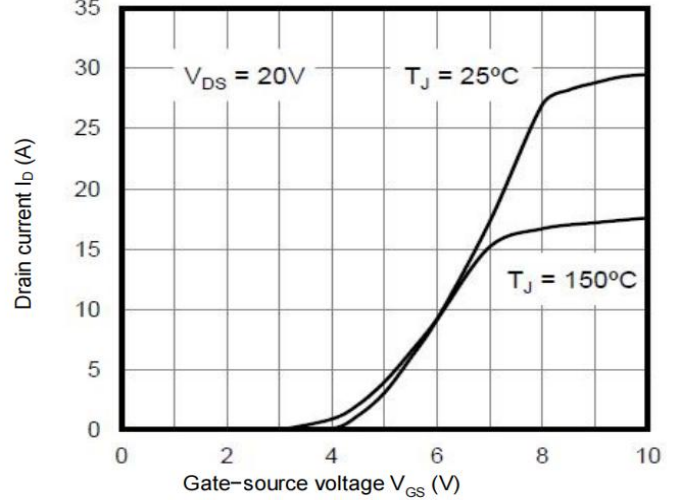


Figure 3. On-Resistance vs. Drain Current

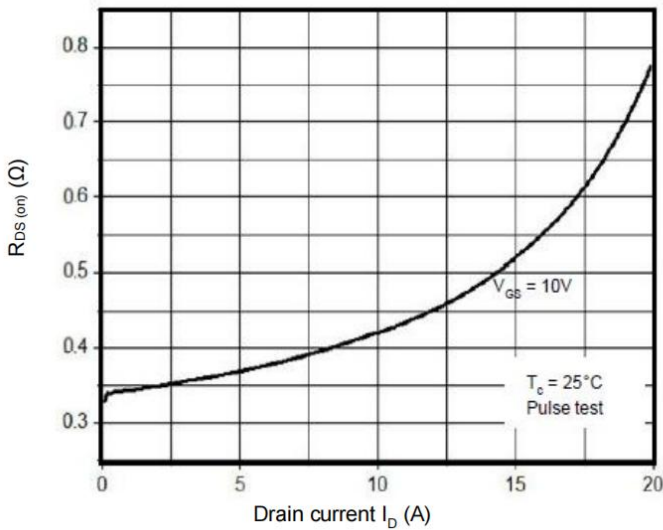


Figure 4. Capacitance Characteristics

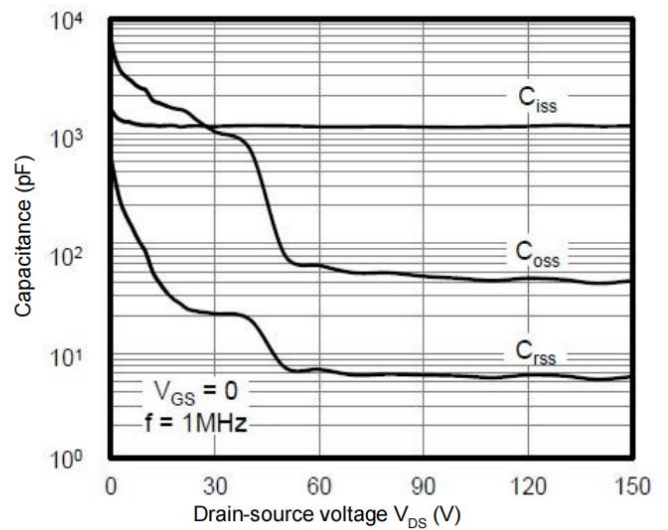


Figure 5. Gate Charge Characteristics

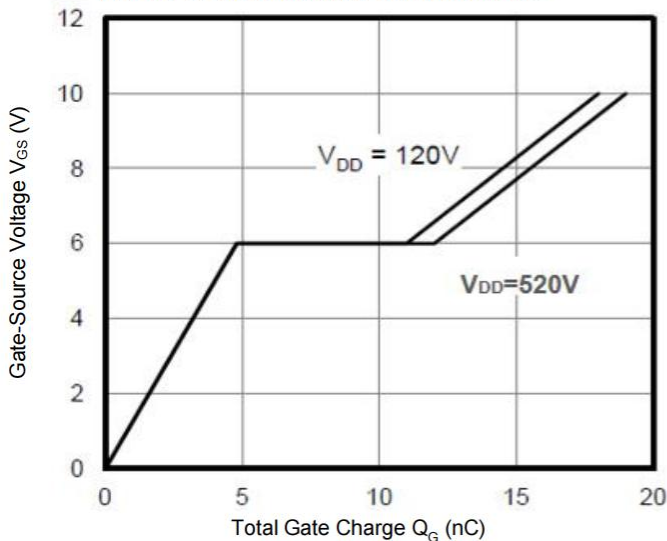


Figure 6. Body Diode Forward Voltage

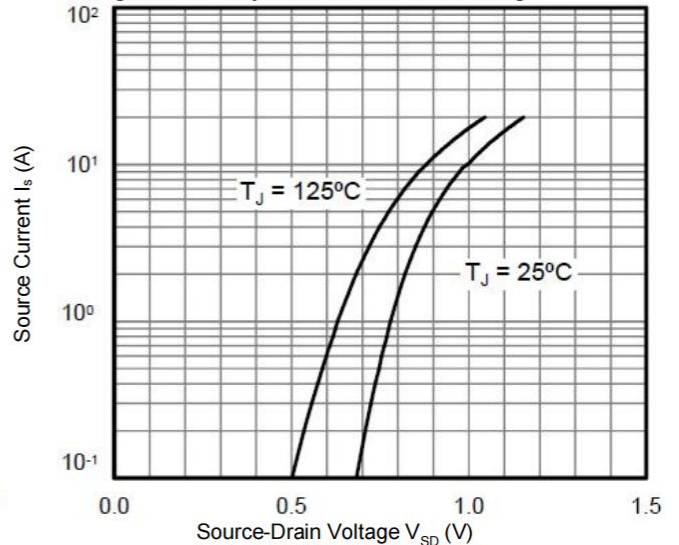


Figure 7. Breakdown Voltage vs. Temperature

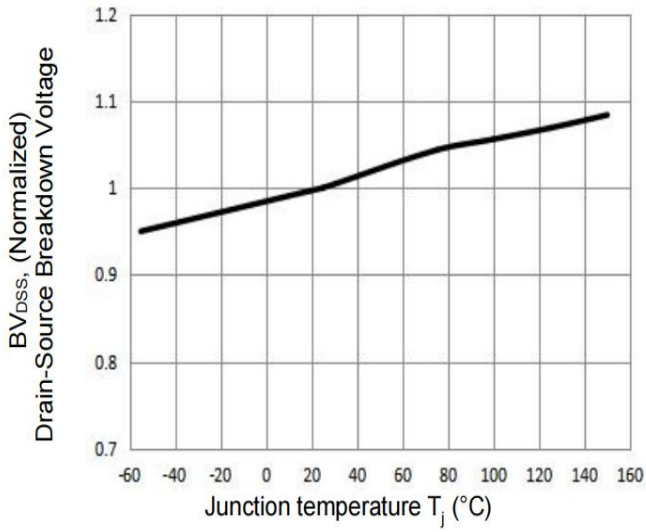


Figure 8. On-Resistance vs. Temperature

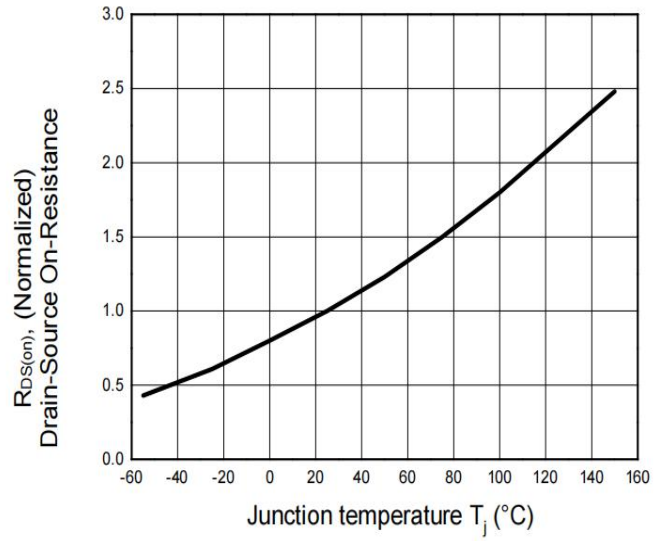
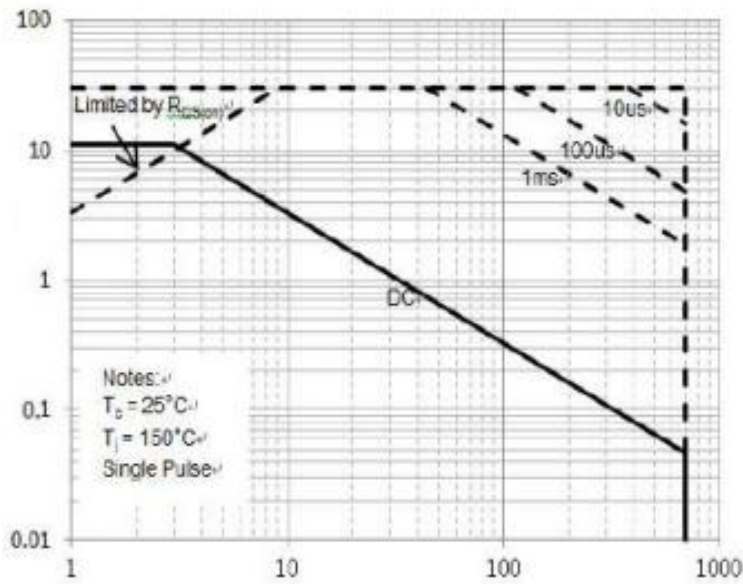


Figure 9. Maximum Safe Operating Area



Test Circuits and Waveforms

Figure A: Gate Charge Test Circuit and Waveform

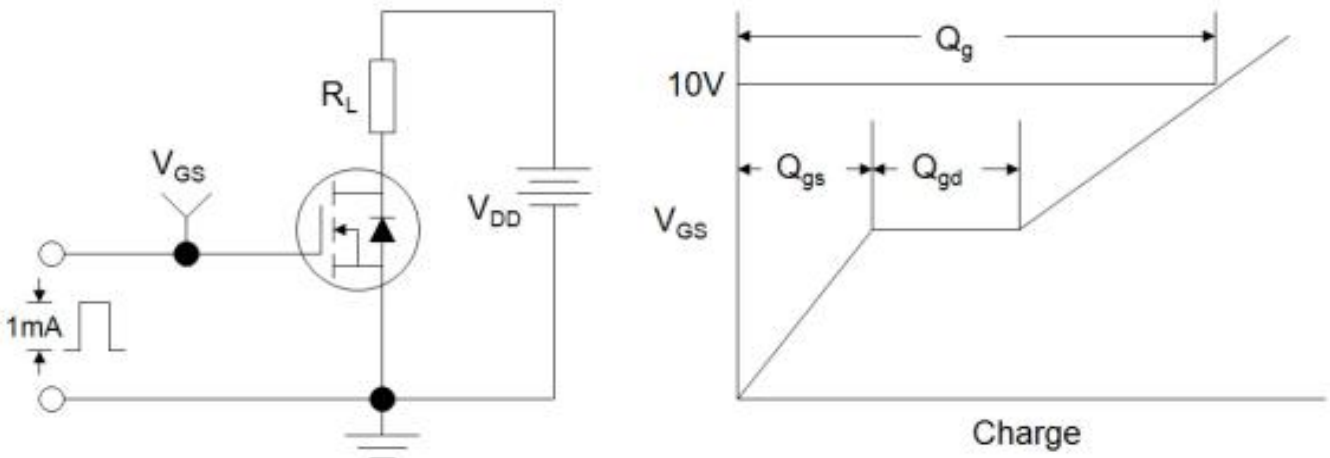


Figure B: Resistive Switching Test Circuit and Waveform

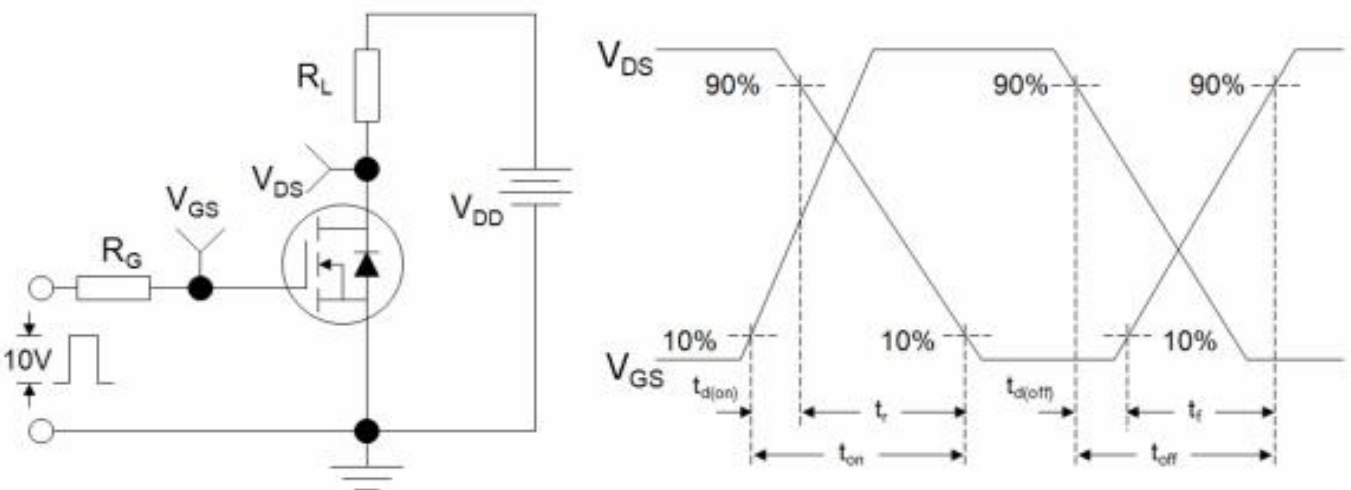
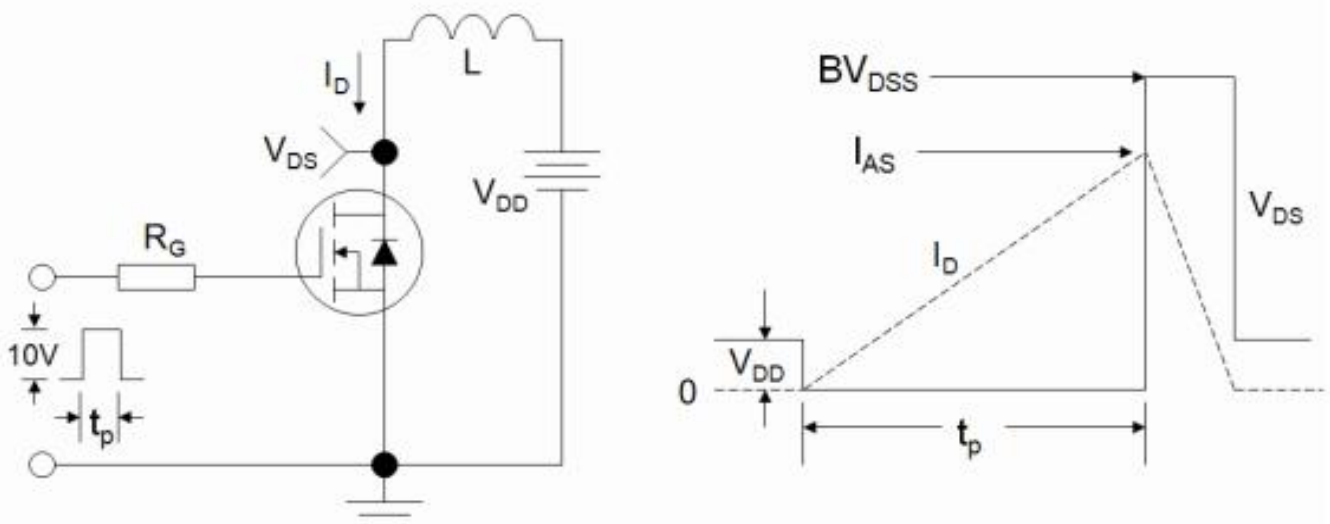
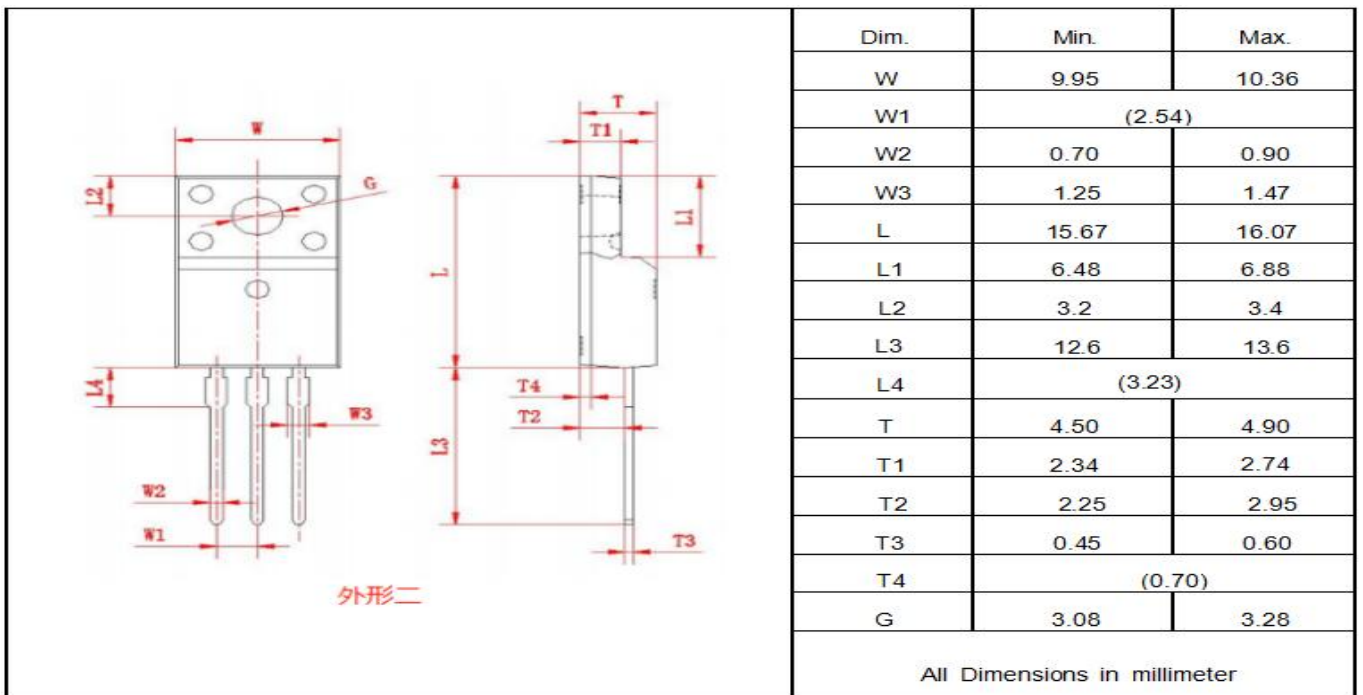
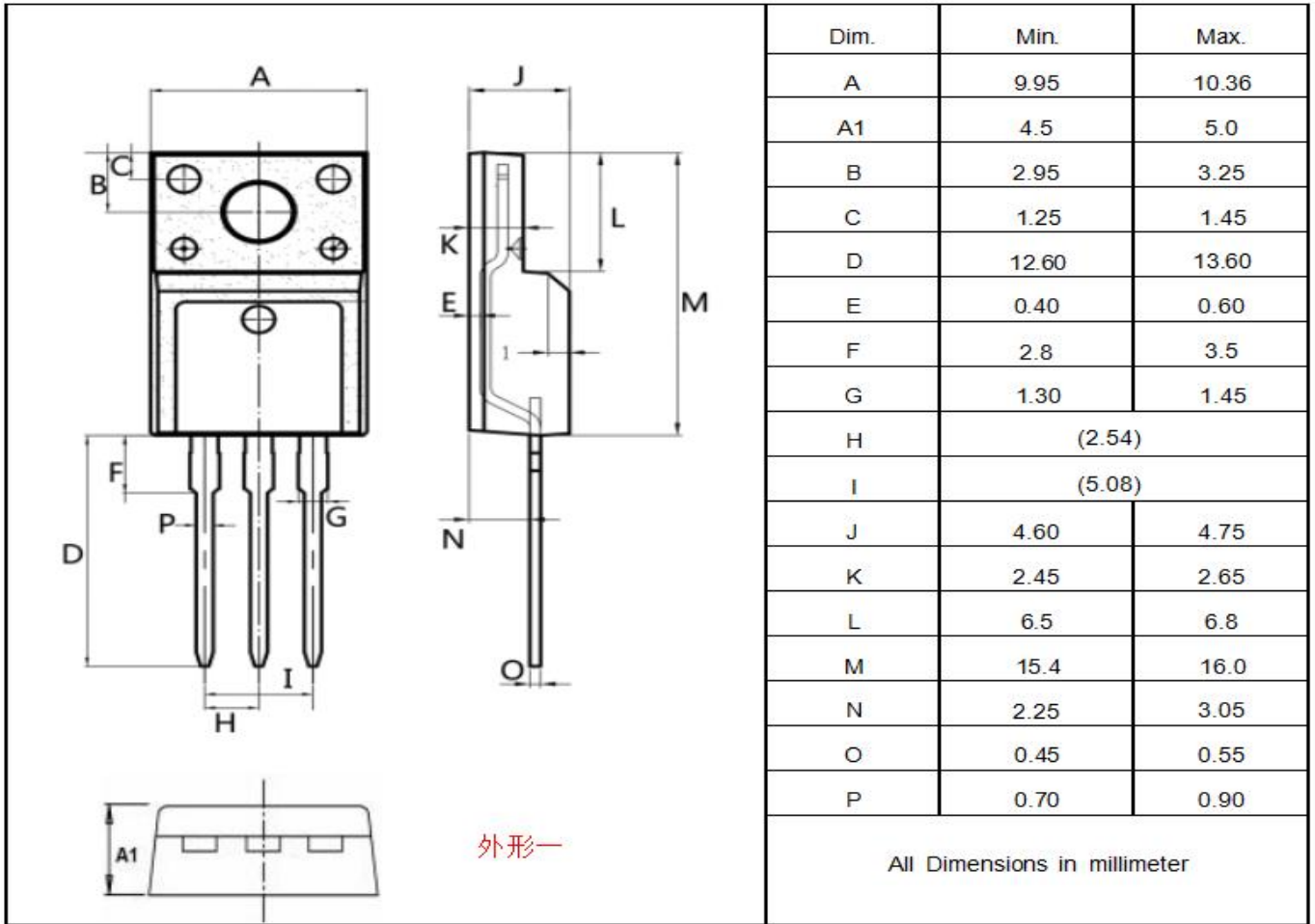


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



Package outline drawing(TO-220F Unit: mm)



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